

MOSFET - Power, Single N-Channel STD Gate, SO8FL

80 V, 3 mΩ, 135 A
NVMFWS3D0N08X

Features

- Low Q_{RR} , Soft Recovery Body Diode
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Synchronous Rectification (SR) in DC-DC and AC-DC
- Primary Switch in Isolated DC-DC Converter
- Motor Drives
- Automotive 48 V System

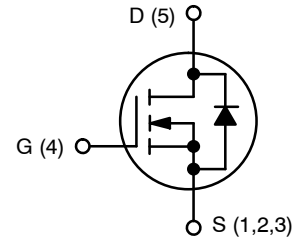
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	80	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Note 1)	I_D	$T_C = 25^\circ\text{C}$	135
		$T_C = 100^\circ\text{C}$	96
Power Dissipation (Note 1)	P_D	119	W
Pulsed Drain Current	I_{DM}	$T_C = 25^\circ\text{C}, t_p = 100 \mu\text{s}$	543
Pulsed Source Current (Body Diode)			
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)	I_S	179	A
Single Pulse Avalanche Energy ($I_{PK} = 47 \text{ A}$) (Note 2)	E_{AS}	110	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$

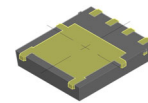
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Actual continuous current will be limited by thermal & electromechanical application board design.
3. E_{AS} of 110 mJ is based on started $T_J = 25^\circ\text{C}$, $I_{AS} = 55 \text{ A}$, $V_{DD} = 64 \text{ V}$, $V_{GS} = 10 \text{ V}$, 100% avalanche tested.

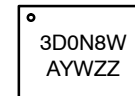
$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	$I_D MAX$
80 V	3 mΩ @ 10 V	135 A



N-CHANNEL MOSFET



DFNW5 (SO-8FL)
CASE 507BA



3D0N8W = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Assembly Lot Code

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 3 of this data sheet.

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THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.26	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	39	

- Surface-mounted on FR4 board using 1 in² pad size, 1 oz. Cu pad.
- $R_{\theta JA}$ is determined by the user's board design.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	80			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = 1\text{ mA}$, Referenced to 25°C		31.6		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{ V}, T_J = 25^\circ\text{C}$			1	μA
		$V_{DS} = 80\text{ V}, T_J = 125^\circ\text{C}$			250	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			100	nA

ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 31\text{ A}$		2.6	3.0	mΩ
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 153\text{ μA}$	2.4		3.6	V
Gate Threshold Voltage Temperature Coefficient	$\Delta V_{GS(TH)} / \Delta T_J$	$V_{GS} = V_{DS}, I_D = 153\text{ μA}$		-7.5		mV/°C
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 31\text{ A}$		97		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}, f = 1\text{ MHz}$		2680		pF
Output Capacitance	C_{OSS}			780		
Reverse Transfer Capacitance	C_{RSS}			12		
Output Charge	Q_{OSS}			56		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 6\text{ V}, V_{DD} = 40\text{ V}, I_D = 31\text{ A}$		23		
				38		
Threshold Gate Charge	$Q_{G(TH)}$	$V_{GS} = 10\text{ V}, V_{DD} = 40\text{ V}, I_D = 31\text{ A}$		7		
Gate-to-Source Charge	Q_{GS}			13		
Gate-to-Drain Charge	Q_{GD}			6		
Gate Plateau Voltage	V_{GP}			4.7		V
Gate Resistance	R_G	$f = 1\text{ MHz}$		0.7		Ω

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	Resistive Load, $V_{GS} = 0/10\text{ V}, V_{DD} = 64\text{ V},$ $I_D = 31\text{ A}, R_G = 2.5\text{ Ω}$		22		ns
Rise Time	t_r			8		
Turn-Off Delay Time	$t_{d(OFF)}$			33		
Fall Time	t_f			5		

SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 31\text{ A}, T_J = 25^\circ\text{C}$		0.82	1.2	V
		$V_{GS} = 0\text{ V}, I_S = 31\text{ A}, T_J = 125^\circ\text{C}$		0.66		

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
SOURCE-TO-DRAIN DIODE CHARACTERISTICS						
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, di/dt = 1000 A/μs, I _S = 31 A, V _{DD} = 64 V		22		ns
Charge Time	t _a			13		
Discharge Time	t _b			9		
Reverse Recovery Charge	Q _{RR}			150		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NVMFWS3D0N08XT1G	3D0N8W	DFNW5 (Pb-Free)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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TYPICAL CHARACTERISTICS

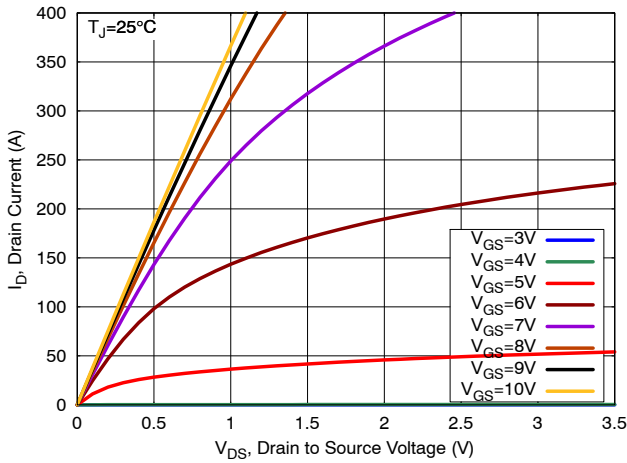


Figure 1. On-Region Characteristics

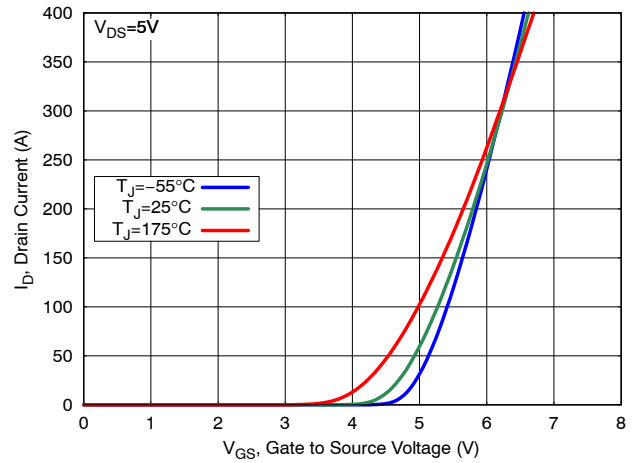


Figure 2. Transfer Characteristics

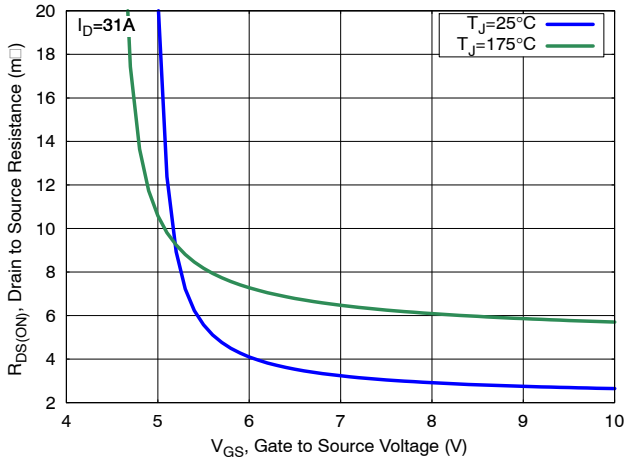


Figure 3. On-Resistance vs. Gate Voltage

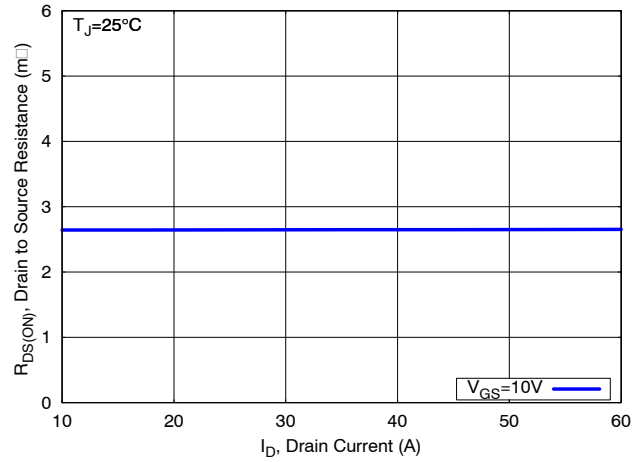


Figure 4. On-Resistance vs. Drain Current

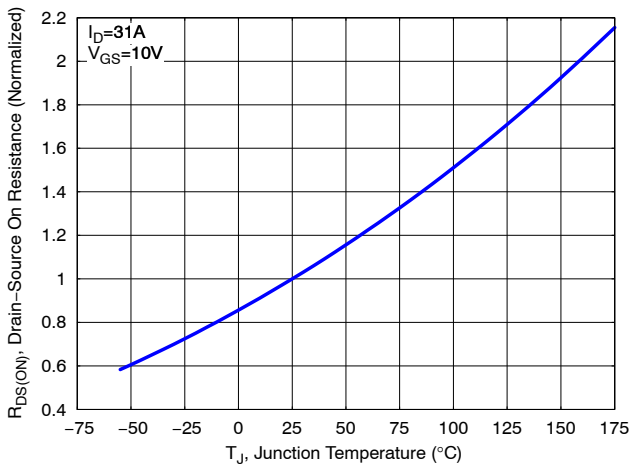


Figure 5. Normalized ON Resistance vs. Junction Temperature

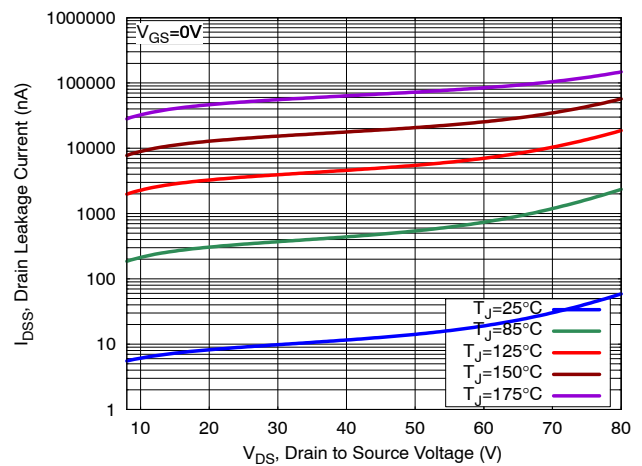


Figure 6. Drain Leakage Current vs. Drain Voltage

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TYPICAL CHARACTERISTICS

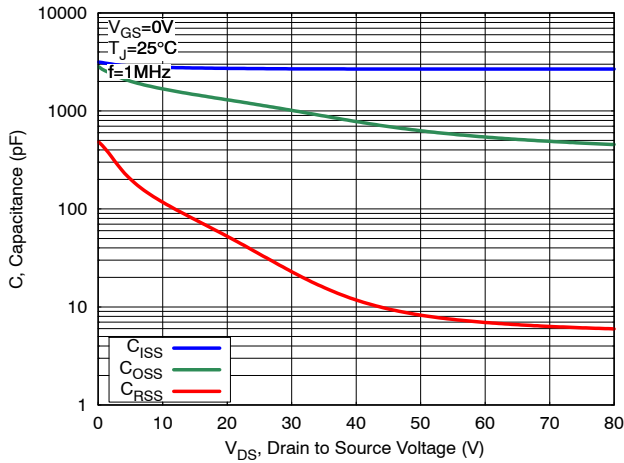


Figure 7. Capacitance Characteristics

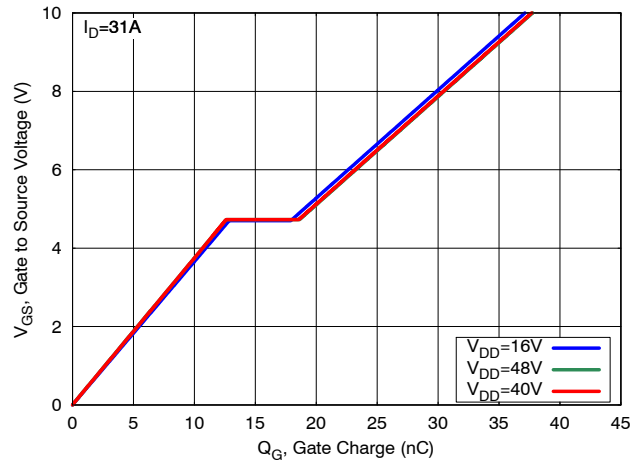


Figure 8. Gate Charge Characteristics

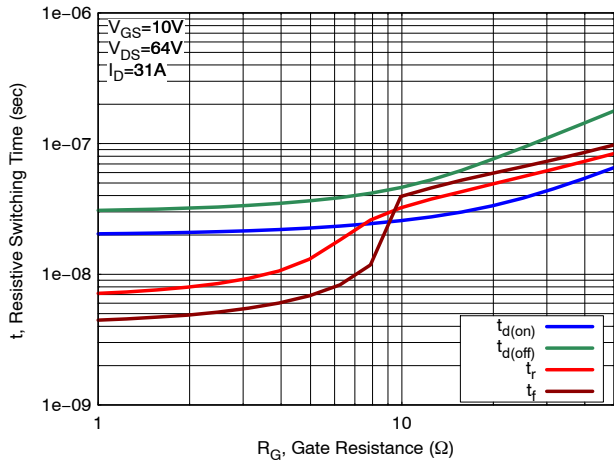


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

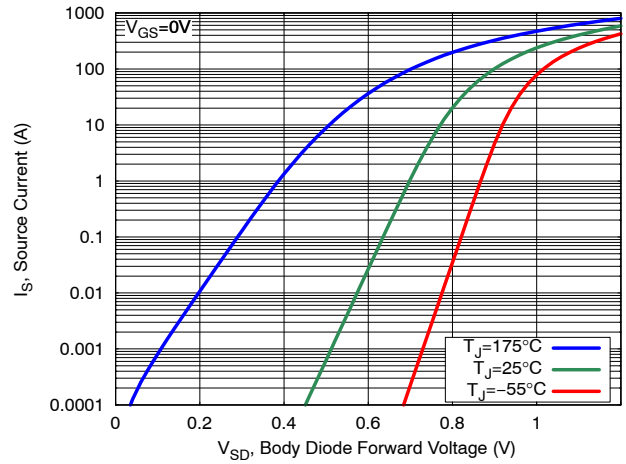


Figure 10. Diode Forward Characteristics

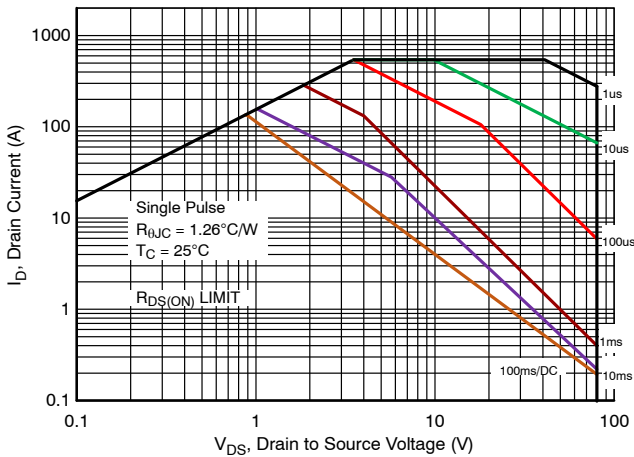


Figure 11. Safe Operating Area (SOA)

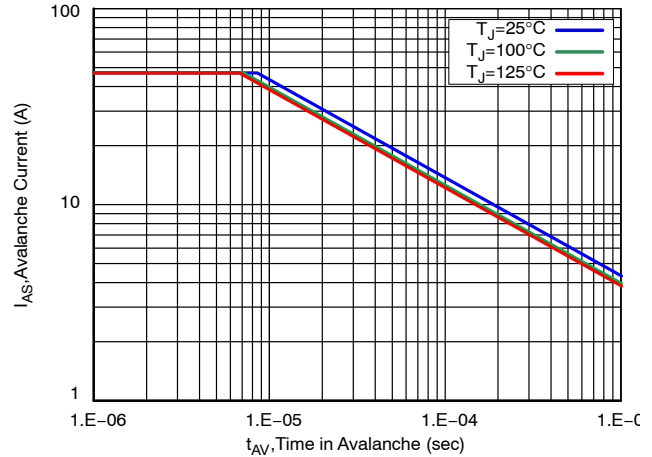


Figure 12. Avalanche Current vs. Pulse Time (UIS)

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TYPICAL CHARACTERISTICS

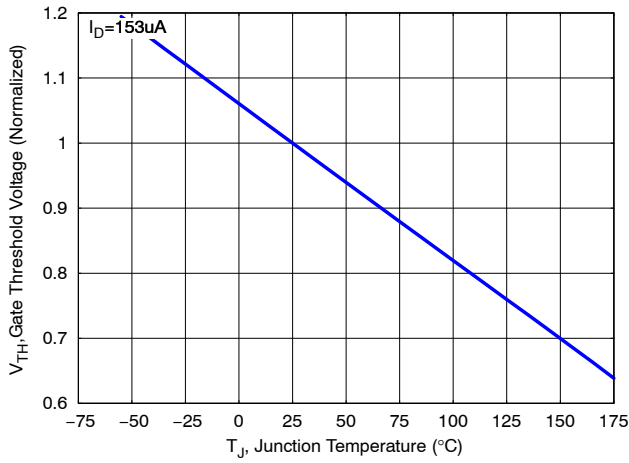


Figure 13. Gate Threshold Voltage vs Junction Temperature

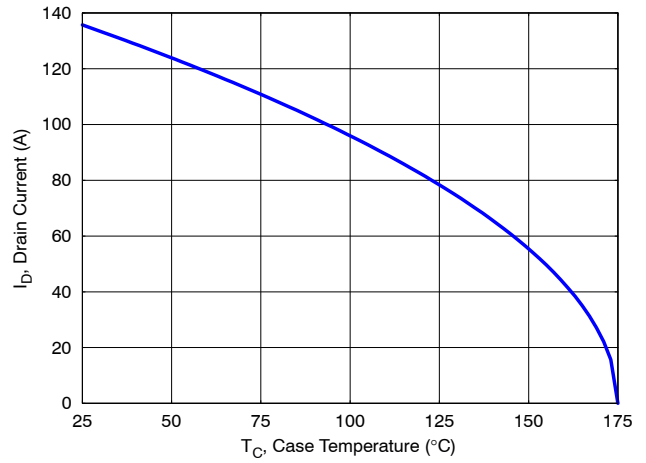


Figure 14. Maximum Current vs. Case Temperature

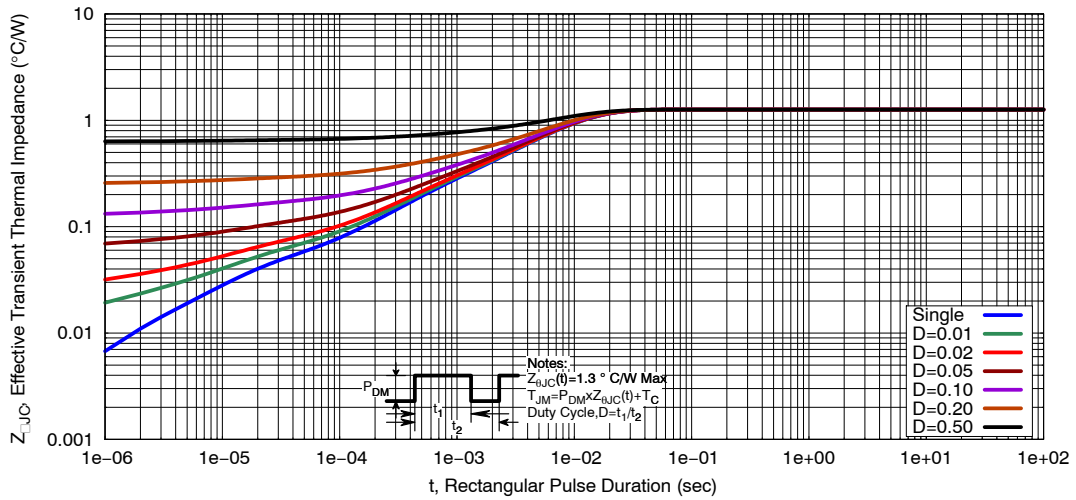
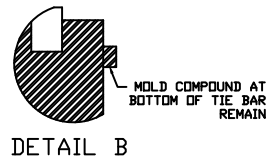
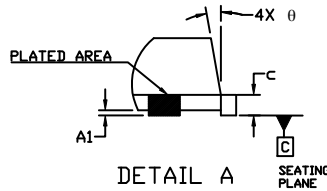
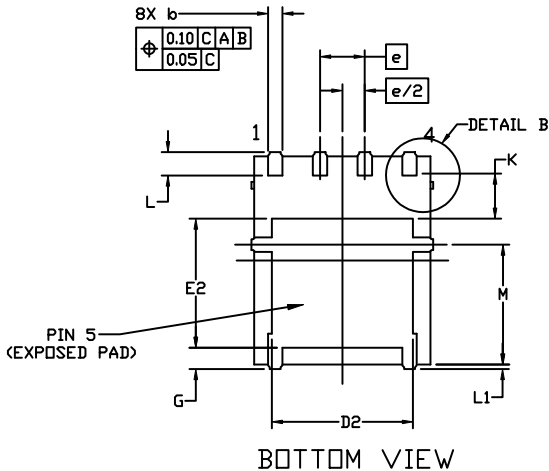
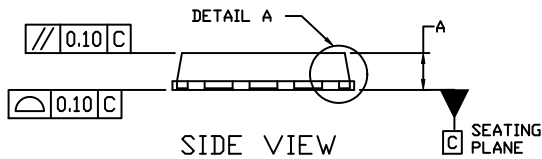
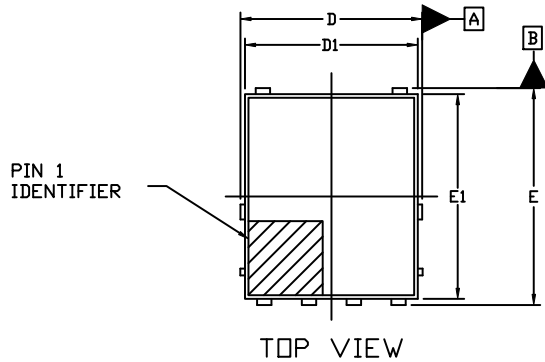


Figure 15. Transient Thermal Response

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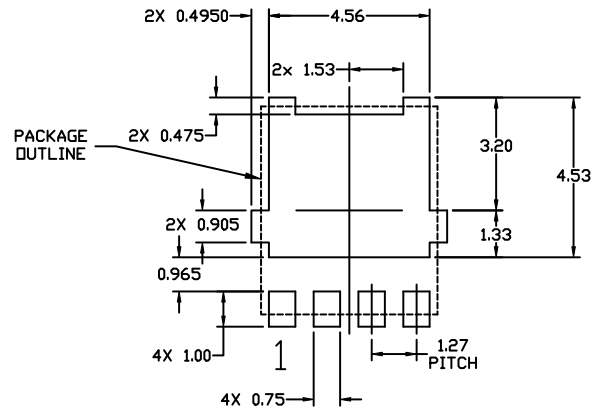
PACKAGE DIMENSIONS

DFNW5 5x6 (FULL-CUT SO8FL WF) CASE 507BA ISSUE A



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
 4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.150 REF		
M	3.00	3.40	3.80
θ	0°	---	12°



RECOMMENDED MOUNTING FOOTPRINT

- * For additional information on our Pb-Free strategy and soldering details, please download the [DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D](#).

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